















TS3A24159 SCDS238D - MARCH 2007 - REVISED JULY 2015

TS3A24159 0.3-Ω 2-Channel SPDT Bidirectional Analog Switch

Dual-Channel 2:1 Multiplexer and Demultiplexer

Features

- Specified Break-Before-Make Switching
- Low ON-State Resistance (0.3 Ω Max)
- Low Charge Injection
- **Excellent ON-State Resistance Matching**
- Low Total Harmonic Distortion (THD)
- 1.65-V to 3.6-V Single-Supply Operation
- Control Inputs Are 1.8-V Logic Compatible
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

Applications

- Cell Phones
- **PDAs**
- Portable Instrumentation
- Audio and Video Signal Routing
- Low-Voltage Data-Acquisition Systems
- Communication Circuits
- Modems
- Hard Drives
- Computer Peripherals
- Wireless Terminals and Peripherals

3 Description

The TS3A24159 is a 2-channel single-pole doublethrow (SPDT) bidirectional analog switch that is designed to operate from 1.65 V to 3.6 V. It offers low ON-state resistance and excellent **ON-state** resistance matching with the break-before-make feature, to prevent signal distortion during the transferring of a signal from one channel to another. The device has excellent total harmonic distortion (THD) performance, low ON-state resistence, and consumes very low power. These are some of the features that make this device suitable for a variety of markets and many different applications.

Device Information⁽¹⁾

PART NUMBER	RT NUMBER PACKAGE BODY SIZE		
	VSSOP (10)	3.00 mm × 3.00 mm	
TS3A24159	VSON (10)	3.00 mm × 3.00 mm	
	DSBGA (10)	1.86 mm × 1.35 mm	

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Functional Block Diagram

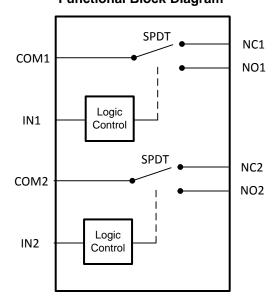




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (February 2008) to Revision D

Page



5 Pin Configuration and Functions

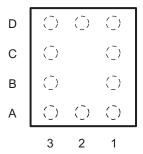


Pin Functions - VSSOP and VSON

			This and the terms of the terms
	PIN	1/0	DESCRIPTION
NO.	NAME	1/0	DESCRIPTION
1	V_{CC}	_	Power Supply
2	NO1	I/O	Normally Open Signal Path
3	COM1	I/O	Common Signal Path
4	IN1	I	Digital Control to Connect COM to NO or NC
5	NC1	I/O	Normally Closed Signal Path
6	GND	_	Ground
7	NC2	I/O	Normally Closed Signal Path
8	IN2	I	Digital Control to Connect COM to NO or NC
9	COM2	I/O	Common Signal Path
10	NO2	I/O	Normally Open Signal Path



YZP Package 10-Pin DSBGA Top-Through View



YZP Package Terminal Assignments

D	NO2	V _{CC}	NO1
С	COM2		COM1
В	IN2		IN1
Α	NC2	GND	NC1
	3	2	1

Pin Functions - DSBGA

	PIN	1/0	DESCRIPTION
NO.	NAME	I/O	DESCRIPTION
A1	NC1	I/O	Normally Closed Signal Path
A2	GND	_	Ground
A3	NC2	I/O	Normally Closed Signal Path
B1	IN1	I	Digital Control to Connect COM to NO or NC
В3	IN2	I	Digital Control to Connect COM to NO or NC
C1	COM1	I/O	Common Signal Path
C3	COM2	I/O	Common Signal Path
D1	NO1	I/O	Normally Open Signal Path
D2	V _{CC}	_	Power Supply
D3	NO2	I/O	Normally Open Signal Path

Product Folder Links: TS3A24159



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1) (2)

			MIN	MAX	UNIT
V_{CC}	Supply voltage ⁽³⁾		-0.5	3.6	V
$V_{NC} \ V_{NO} \ V_{COM}$	Signal voltage ⁽³⁾ (4) (5)			V _{CC} + 0.5	V
I _{I/OK}	Analog port diode current	V_{NC} , V_{NO} , $V_{COM} < 0$	-50	50	mA
I _{NC}			-300	300	_
I _{NO} I _{COM}	ON-state peak switch current ⁽⁶⁾	V_{NC} , V_{NO} , $V_{COM} = 0$ to V_{CC}	-500	500	mA
V_{IN}	Digital input voltage		-0.5	3.6	V
I _{IK}	Digital input clamp current (3) (4)	V _I < 0	-50		mA
I _{CC}	Continuous current through V _{CC} Continuous current through GND			100	mA
I_{GND}			-100		mA
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- 2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Pulse at 1-ms duration <10% duty cycle

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD) Electrostatic discharge	Flootrootatio diacharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	2000	V
	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CC}	Supply Voltage	1.65	3.6	V
V _{NC} V _{NO} V _{COM}	Signal Voltage	0	V _{CC}	V
V_{IN}	Digital Input Voltage	0	V_{CC}	V

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

TEXAS INSTRUMENTS

6.4 Thermal Information

			TS3A24159				
	THERMAL METRIC ⁽¹⁾	DGS (VSSOP)	DRC (VSON)	YZP (DSBGA)	UNIT		
		10 PINS	10 PINS	10 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	154	49.4	90.9	°C/W		
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	37.9	71.2	0.3	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	83.6	23.8	8.3	°C/W		
ΨЈТ	Junction-to-top characterization parameter	1.4	2.2	3.2	°C/W		
ΨЈВ	Junction-to-board characterization parameter	82.2	23.8	8.3	°C/W		
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	6.1	N/A	°C/W		

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics for 3-V Supply

 $V_{CC} = 2.7 \text{ V}$ to 3.6 V, $T_A = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted) (1)

PARAME	TER	TEST CONDITION	S	T _A	V _{CC}	MIN	TYP	MAX	UNIT
ANALOG SWITCH									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V _{CC}	V
Peak ON		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_{CC}$	Switch ON,	25°C	2.7 V		0.2	0.3	Ω
resistance	r _{peak}	$I_{COM} = -100 \text{ mA},$	See Figure 10	Full	2.1 V			0.35	12
ON-state	r _{on}	V_{NO} or $V_{NC} = 2 V$,	Switch ON,	25°C	2.7 V		0.26	0.3	Ω
resistance	ion	$I_{COM} = -100 \text{ mA},$	See Figure 10	Full	2.1 V			0.34	32
ON-state		V_{NO} or $V_{NC} = 2 \text{ V}, 0.8 \text{ V},$	Switch ON,	25°C	071/		0.01	0.05	
resistance match between channels	Δr_{on}	$I_{COM} = -100 \text{ mA},$	See Figure 10	Full	2.7 V			0.05	Ω
ON-state	r _{on(flat)}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_{CC},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 10	25°C	2.7 V		0.13		Ω
resistance flatness		NO TO	Switch ON,	25°C			0.01	0.04	Ω
			See Figure 10	Full				0.05	
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 1 \text{ V}$, $V_{COM} = 3 \text{ V}$,	Switch OFF,	25°C		-10		10	
OFF leakage current	I _{NO(OFF)}	or V_{NC} or $V_{NO} = 3 \text{ V}, V_{COM} = 1 \text{ V},$	See Figure 11	Full	3.6 V	-50		50	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 1 V$, $V_{COM} = Open$,	Switch ON.	25°C		-10		10	
ON leakage current	I _{NO(ON)}	or V_{NC} or $V_{NO} = 3 \text{ V}, V_{COM} = \text{Open},$	See Figure 12	Full	3.6 V	-100		100	nA
COM		V_{NC} or V_{NO} = Open, V_{COM} = 1 V,	Switch ON.	25°C		-10		10	
ON leakage current	I _{COM(ON)}	or V_{NC} or V_{NO} = Open, V_{COM} = 3 V,	See Figure 12	Full	3.6 V	-100		100	nA
DIGITAL CONTROL	INPUTS (IN1,	, IN2) ⁽²⁾							
Input logic high	V_{IH}			Full		1.4			V
Input logic low	V_{IL}			Full				0.5	V
Input leakage	akane	25°C	3.6 V	-40	5	40			
current	I_{IH},I_{IL}	$V_1 = 3.6 \text{ V or } 0$		Full	3.0 V	-50		50	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

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⁽²⁾ All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



Electrical Characteristics for 3-V Supply (continued)

 V_{CC} = 2.7 V to 3.6 V, T_A = -40°C to 85°C (unless otherwise noted) $^{(1)}$

PARAME	TER	TEST CONDIT	IONS	T _A	V _{CC}	MIN TYP	MAX	UNIT
DYNAMIC		•						
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 1 \text{ nF},$ See Figure 19	25°C	3 V	9		рС
NC, NO OFF capacitance	$C_{NC(OFF)}, \ C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{CC}$ or GND, Switch OFF,	See Figure 13	25°C	3 V	90		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{CC}$ or GND, Switch ON,	See Figure 13	25°C	3 V	224		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V _{CC} or GND, Switch ON,	See Figure 13	25°C	3 V	250		pF
Digital input capacitance	C _I	$V_{IN} = V_{CC}$ or GND,	See Figure 13	25°C	3 V	2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	3 V	23		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 17	25°C	3 V	-72		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 18	25°C	3 V	-96		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 20	25°C	3 V	0.003%		
SUPPLY					•			
Positive supply	Icc	$V_{IN} = V_{CC}$ or GND		25°C	3.6 V	15	100	nA
current	'CC	AIN - ACC OL QIAD		Full		1		μΑ

6.6 Electrical Characteristics for 2.5-V Supply

 V_{CC} = 2.3 V to 2.7 V, T_A = -40°C to 85°C (unless otherwise noted) ⁽¹⁾

PARAME'	TER	TEST CONDITIONS		T _A	V _{CC}	MIN	TYP	MAX	UNIT
ANALOG SWITCH									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V_{CC}	V
Peak ON		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_{CC},$	Switch ON,	25°C				0.35	_
resistance	r _{peak}	$I_{COM} = -8 \text{ mA},$	See Figure 10	Full	2.3 V			0.45	Ω
ON-state		V_{NO} or $V_{NC} = 1.8 \text{ V}$,	Switch ON,	25°C					
resistance	r _{on}	$I_{COM} = -8 \text{ mA},$	See Figure 10	Full	2.3 V			0.4	Ω
ON-state		V _{NO} or V _{NC} = 1.8 V, 0.8 V,	Switch ON,	25°C	2.3 V		0.01	0.05	Ω
resistance match between channels	Δr_{on}	$I_{COM} = -8 \text{ mA},$	See Figure 10	Full			0.05	0.05	
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_{CC},$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 10	25°C	221		0.05		
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.8 \text{ V}, 1.8 \text{ V},$	Switch ON,	25°C	2.3 V		0.03	0.08	Ω
		$I_{COM} = -8 \text{ mA},$	See Figure 10	Full				0.1	
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0.5 \text{ V}$, $V_{COM} = 2.2 \text{ V}$,	Switch OFF,	25°C		-10		10	
OFF leakage current	I _{NO(OFF)}	or V_{NC} or $V_{NO} = 2.2 \text{ V}$, $V_{COM} = 0.5 \text{ V}$,	See Figure 11	Full	2.7 V	-50		50	nA
NC, NO		V_{NC} or $V_{NO} = 0.5 \text{ V}$, $V_{COM} = \text{Open}$,		25°C		-10		10	
ON leakage current	I _{NO(ON)}	or V_{NC} or $V_{NO} = 2.2 \text{ V}$, $V_{COM} = \text{Open}$,	See Figure 12	Full	2.7 V	-100		100	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.



Electrical Characteristics for 2.5-V Supply (continued)

 V_{CC} = 2.3 V to 2.7 V, T_A = -40°C to 85°C (unless otherwise noted) ⁽¹⁾

PARAME	TER	TEST CONDITION	NS	T _A	V _{CC}	MIN TY	P MAX	UNIT
ANALOG SWITCH	(continued)							
COM		V _{NC} or V _{NO} = Open, V _{COM} = 0.5		25°C		-10	10	
ON leakage current	I _{COM(ON)}	or V_{NC} or V_{NO} = Open, V_{COM} = 2.2	See V, Figure 12	Full	2.7 V	-100	100	nA
DIGITAL CONTROL	INPUTS (IN1	, IN2) ⁽²⁾		+	1	•		
Input logic high	V_{IH}			Full		1.25		V
Input logic low	V_{IL}			Full			0.5	V
Input leakage		V 27V 250		25°C	271/	-40	5 40	
current	I _{IH} , I _{IL}	$V_1 = 2.7 \text{ V or } 0$		Full	2.7 V	-50	50	nA
DYNAMIC								
Charge injection	$Q_{\mathbb{C}}$	V _{GEN} = 0, R _{GEN} = 0,	$C_L = 1 \text{ nF},$ See Figure 19	25°C	2.5 V		8	рС
NC, NO OFF capacitance	$C_{NC(OFF)}, \ C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{CC}$ or GND, Switch OFF,	See Figure 13	25°C	2.5 V		90	pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{CC}$ or GND, Switch ON,	See Figure 13	25°C	2.5 V	2	50	pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V _{CC} or GND, Switch ON,	See Figure 13	25°C	2.5 V	2	50	pF
Digital input capacitance	C_{I}	$V_I = V_{CC}$ or GND,	See Figure 13	25°C	2.5 V		2	pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	2.5 V	:	23	MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 17	25°C	2.5 V		72	dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	See Figure 18	25°C	2.5 V		96	dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 20	25°C	2.5 V	0.003	%	
SUPPLY								
Positive supply current	I _{CC}	V _I = V _{CC} or GND		25°C	2.7 V		10 100 00	nA
Carrott				Full		1	JU	

⁽²⁾ All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

6.7 Electrical Characteristics for 1.8-V Supply

 V_{CC} = 1.65 V to 1.95 V, T_{A} = $-40^{\circ} C$ to 85°C (unless otherwise noted) $^{(1)}$

PARAM	IETER	TEST CONDI	T _A	V _{CC}	MIN	TYP	MAX	UNIT	
ANALOG SWITC	:H	!	-						
Analog signal range	$V_{\text{COM}}, V_{\text{NO}}, V_{\text{NC}}$					0		V _{CC}	٧
Peak ON	r .	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_{CC},$	Switch ON,	25°C	1.65 V		0.4	0.7	Ω
resistance	r _{peak}	$I_{COM} = -2 \text{ mA},$	See Figure 10	Full	1.05 V			0.8	22
ON-state	_	V_{NO} or $V_{NC} = 1.5 \text{ V}$,	Switch ON,	25°C	1.65 V		0.3	0.45	C
resistance	r _{on}	V_{NO} or $V_{NC} = 1.5 V$, $I_{COM} = -2 \text{ mA}$,	See Figure 10	Full	1.05 V			0.5	12

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum



Electrical Characteristics for 1.8-V Supply (continued)

 V_{CC} = 1.65 V to 1.95 V, T_A = -40°C to 85°C (unless otherwise noted) $^{(1)}$

PARAME	TER	TEST CONDITIONS	3	T _A	V _{CC}	MIN TY	MAX	UNIT
ANALOG SWITCH	(continued)				•	II.		
ON-state				25°C		0.0	2 0.04	
resistance match between channels	Δr_{on}	V_{NO} or $V_{NC} = 0.6 \text{ V}$, 1.5 V, $I_{COM} = -2 \text{ mA}$,	Switch ON, See Figure 10	Full	1.65 V		0.05	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_{CC},$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 10	25°C		0.13	3	
resistance flatness	$r_{on(flat)}$	V_{NO} or $V_{NC} = 0.6 \text{ V}$, 1.5 V,	Switch ON,	25°C	1.65 V	0.0	3 0.15	Ω
		$I_{COM} = -8 \text{ mA},$	See Figure 10	Full			0.2	
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0.3 \text{ V}$, $V_{COM} = 1.65 \text{ V}$,	Switch OFF,	25°C		-10	10	
OFF leakage current	I _{NO(OFF)}	or V_{NC} or $V_{NO} = 1.65 \text{ V}$, $V_{COM} = 0.3 \text{ V}$,	See Figure 11	Full	1.95	-50	50	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 0.3 \text{ V}$, $V_{COM} = \text{Open}$,	Switch ON,	25°C		-10	10	
ON leakage current	I _{NO(ON)}	or V_{NC} or $V_{NO} = 1.65 \text{ V}$, $V_{COM} = \text{Open}$,	See Figure 12	Full	1.95 V	-100	100	nA
COM		V_{NC} or V_{NO} = Open, V_{COM} = 0.3 V,	Switch ON.	25°C		-10	10	
ON leakage current	I _{COM(ON)}	or V_{NC} or V_{NO} = Open, V_{COM} = 1.65 V,	See Figure 12	Full	1.95 V	-100	100	nA
DIGITAL CONTRO		1, IN2) ⁽²⁾						
Input logic high	V_{IH}			Full		1		V
Input logic low	V_{IL}			Full			0.4	V
Input leakage	I _{IH} , I _{IL}	V _I = 1.95 V or 0		25°C	1.95 V	-40 ·	5 40	nA
current	'IH' 'IL	V = 1.55 V 61 0		Full	1.55 V	-50	50	11/4
DYNAMIC						T		,
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 19	25°C	1.8 V		5	рC
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{CC}$ or GND, Switch OFF,	See Figure 13	25°C	1.8 V	90)	pF
NC, NO ON capacitance	$C_{NC(ON)}, \\ C_{NO(ON)}$	V_{NC} or $V_{NO} = V_{CC}$ or GND, Switch ON,	See Figure 13	25°C	1.8 V	250)	pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V _{CC} or GND, Switch ON,	See Figure 13	25°C	1.8 V	250)	pF
Digital input capacitance	C_{IN}	$V_{I} = V_{CC}$ or GND,	See Figure 13	25°C	1.8 V	:	2	pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	1.8 V	23	3	MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	See Figure 17	25°C	1.8 V	-7:	3	dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$,	See Figure 18	25°C	1.8 V	-9	7	dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 20	25°C	1.8 V	0.005%	ó	
SUPPLY			ı		T	T		
Positive supply	I _{CC}	$V_{I} = V_{CC}$ or GND		25°C	1.95 V	100		nΑ
current	•00	1, 100 0. 0.12		Full	1.55 V		700	.,,,

⁽²⁾ All unused digital inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



6.8 Switching Characteristics for a 3-V Supply

 V_{CC} = 2.7 V to 3.6 V, T_A = -40°C to 85°C (unless otherwise noted)⁽¹⁾

PARAME	ETER	TEST CO	NDITIONS	T _A	V _{cc}	MIN	TYP	MAX	UNIT
Dynamic									
				25°C	2.5 V		20	35	
Turnon time	t _{ON}	$V_{COM} = V_{CC},$ $R_L = 50 \Omega$	C _L = 35 pF, See Figure 14	Full	2.3 V to 2.7 V			40	ns
				25°C	2.5 V		12	25	
Turnoff time	t _{OFF}	$V_{COM} = V_{CC},$ $R_L = 50 \Omega$	C _L = 35 pF, See Figure 14	Full	2.3 V to 2.7 V			30	ns
				25°C	2.5 V	1	10	25	
Break-before- make time	$t_{BBM} \qquad \begin{array}{l} V_{NC} = V_{NO} = V_{CC}, \\ R_{L} = 50 \ \Omega \end{array}$	$V_{NC} = V_{NO} = V_{CC},$ $R_{L} = 50 \Omega$	C _L = 35 pF, See Figure 15	Full	2.3 V to 2.7 V	0.5		30	ns

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

6.9 Switching Characteristics for a 2.5-V Supply

 V_{CC} = 2.3 V to 2.7 V, T_A = -40°C to 85°C (unless otherwise noted) ⁽¹⁾

PARAMI	ETER	TEST COM	TA	V _{CC}	MIN	TYP	MAX	UNIT	
Dynamic									
				25°C	1.8 V		23	45	
Turnon time	t _{ON}	$V_{COM} = V_{CC},$ $R_L = 50 \Omega$	C _L = 35 pF, See Figure 14	Full	1.65 V to 1.96 V			50	ns
				25°C	1.8 V		17	27	
Turnoff time	t _{OFF}	$V_{COM} = V_{CC},$ $R_L = 50 \Omega$	C _L = 35 pF, See Figure 14	Full	1.65 V to 1.96 V			30	ns
				25°C	1.8 V	2	14	30	
Break-before- make time	$t_{BBM} \qquad \begin{array}{c} V_{NC} = V_{NO} = V_{CC}, \\ R_L = 50 \ \Omega \end{array}$		C _L = 35 pF, See Figure 15	Full	1.65 V to 1.96 V	1		35	ns

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

6.10 Switching Characteristics for a 1.8-V Supply

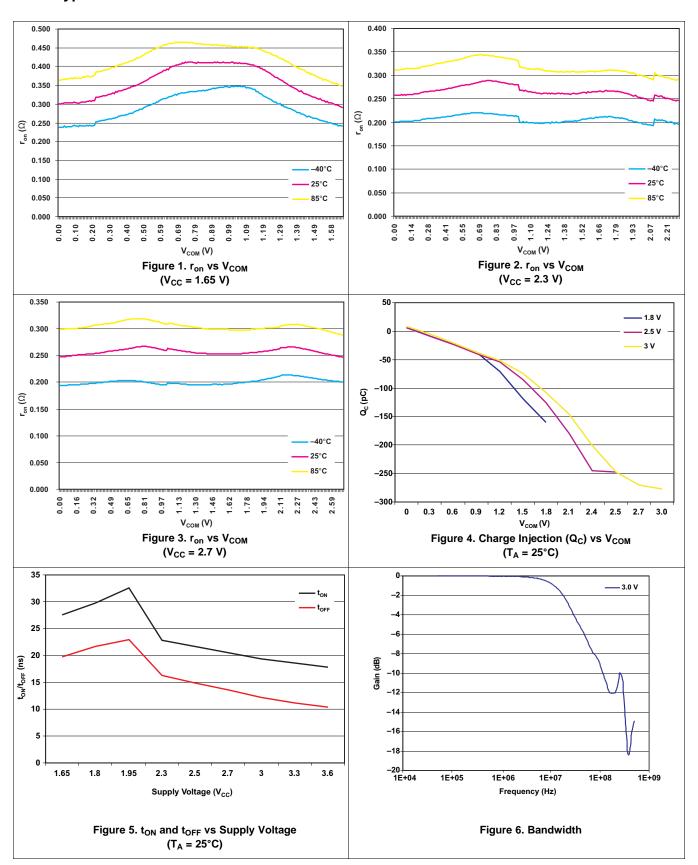
 V_{CC} = 1.65 V to 1.95 V, T_A = -40°C to 85°C (unless otherwise noted) $^{(1)}$

PARAMI	ETER	TEST CO	NDITIONS	TA	V _{CC}	MIN	TYP	MAX	UNIT
Dynamic		•			•			•	
				25°C	1.8 V		53	75	
Turnon time	t _{ON}	$V_{COM} = V_{CC},$ $R_L = 50 \Omega$	C _L = 35 pF, See Figure 14	Full	1.65 V to 1.96 V			80	ns
				25°C	1.8 V		24	35	
Turnoff time	t _{OFF}	$V_{COM} = V_{CC},$ $R_L = 50 \Omega$	C _L = 35 pF, See Figure 14	Full	1.65 V to 1.96 V			40	ns
				25°C	1.8 V	2	30	40	
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_{CC},$ $R_{L} = 50 \Omega$	C _L = 35 pF, See Figure 15	Full	1.65 V to 1.96 V	1		50	ns

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

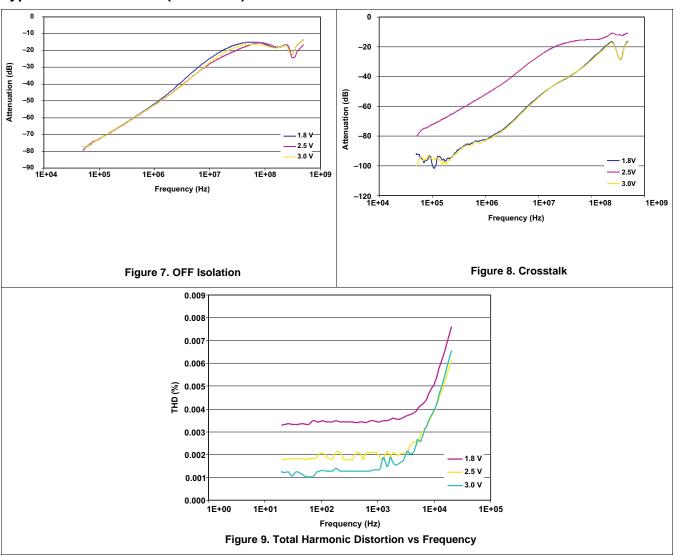


6.11 Typical Characteristics





Typical Characteristics (continued)





7 Parameter Measurement Information

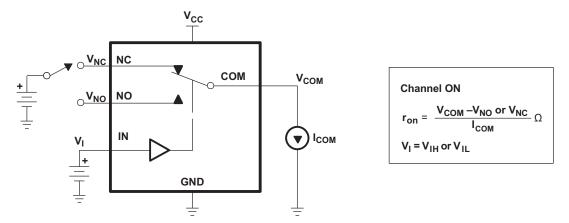


Figure 10. ON-State Resistance

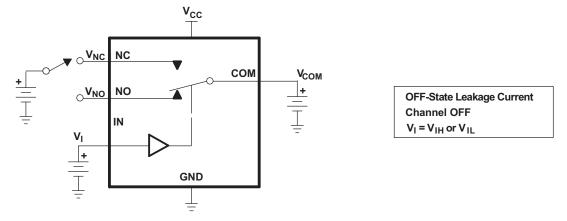


Figure 11. OFF-State Leakage Current (I_{NC(OFF)}, I_{NC(PWROFF)}, I_{NO(OFF)}, I_{NO(PWROFF)}, I_{COM(PWROFF)})

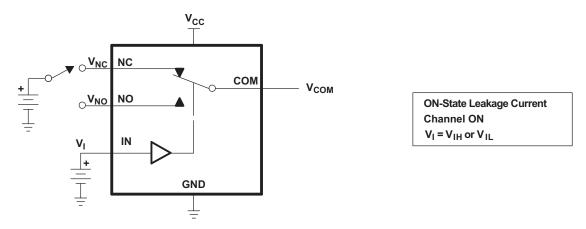


Figure 12. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$, $I_{NO(ON)}$)

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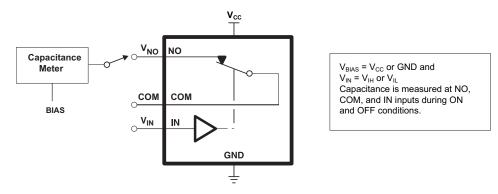
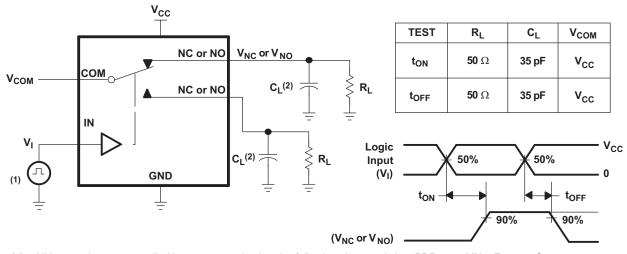
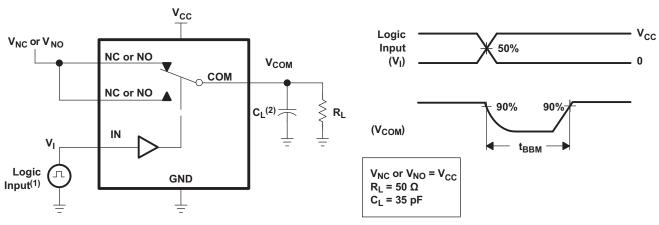


Figure 13. Capacitance C_{I} , $C_{NC(OFF)}$, $C_{NO(OFF)}$, $C_{NC(ON)}$, $C_{NO(ON)}$)



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- (2) C_L includes probe and jig capacitance.

Figure 14. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- (2) C_L includes probe and jig capacitance.

Figure 15. Break-Before-Make Time (t_{BBM})



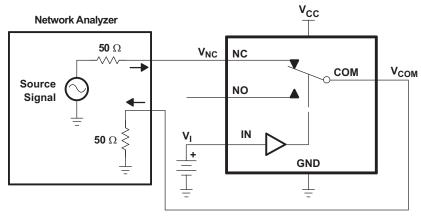


Figure 16. Bandwidth (BW)

Channel ON: NC to COM $V_I = V_{CC}$ or GND

Network Analyzer Setup

Source Power = 0 dBm (632-mV P-P at 50- Ω load)

DC Bias = 350 mV

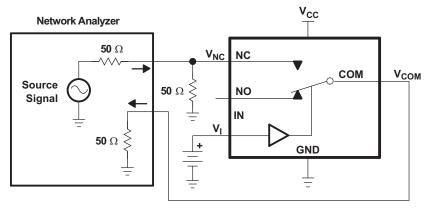


Figure 17. OFF Isolation (O_{ISO})

Channel OFF: NC to COM
V_I = V_{CC} or GND

Network Analyzer Setup

Source Power = 0 dBm (632-mV P-P at 50- Ω load) DC Bias = 350 mV

Figure 18. Crosstalk (X_{TALK})

Channel ON: NC to COM Channel OFF: NO to COM $V_{IN} = V_{CC}$ or GND

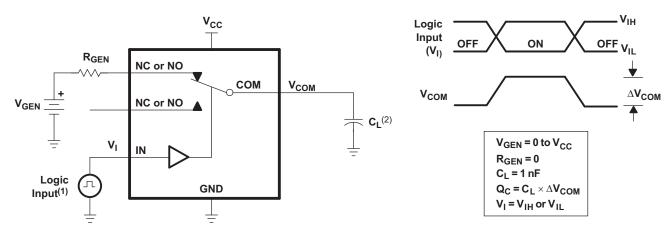
Network Analyzer Setup

Source Power = 0 dBm (632-mV P-P at 50-Ωload)

DC Bias = 350 mV

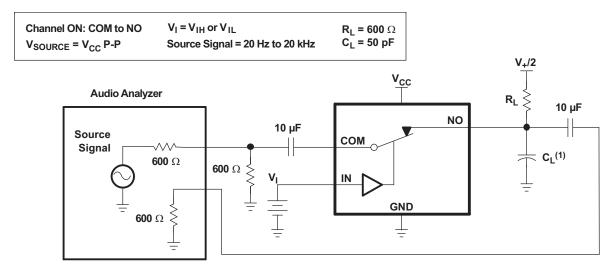
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- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

Figure 19. Charge Injection (Q_C)



A. C_L includes probe and jig capacitance.

Figure 20. Total Harmonic Distortion (THD)

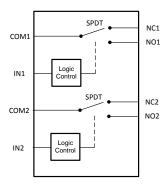


8 Detailed Description

8.1 Overview

The TS3A24159 is a 2-channel single-pole double-throw (SPDT) bidirectional analog switch that is designed to operate from 1.65 V to 3.6 V. It offers low ON-state resistance and excellent ON-state resistance matching with the break-before-make feature, to prevent signal distortion during the transferring of a signal from one channel to another. The device has excellent total harmonic distortion (THD) performance, low ON-state resistence, and consumes very low power. These are some of the features make this device suitable for a variety of markets and many different applications.

8.2 Functional Block Diagram



8.3 Feature Description

The TS3A24159 device is bidirectional with two single-pole, double-throw switches. Each of the two switches are controlled independently by two digital signals.

8.4 Device Functional Modes

Table 1. Function Table

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
Н	OFF	ON



9 Application and Implementation

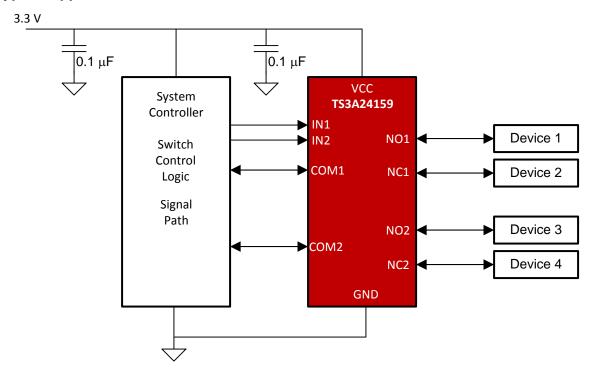
NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The switch of the TS3A23159 device is bidirectional. Hence, NO, NC and COM pins can be used as both inputs or outputs.

9.2 Typical Application



9.2.1 Design Requirements

Ensure that all of the signals passing through the switch are with in the specified ranges to ensure proper performance.

Table 2. Design Parameters

		MIN	MAX	UNIT
V _{CC}	Supply Voltage	1.65	3.6	V
V _{NC} V _{NO} V _{COM}	Signal Voltage	0	V _{cc}	V
V _{IN}	Digital Input Voltage	0	V _{CC}	V



9.2.2 Detailed Design Procedure

The TS3A23159 device can be properly operated without any external components. However, it is recommended that unused pins must be connected to ground through a $50-\Omega$ resistor to prevent signal reflections back into the device. It is also recommended that the digital control pins (IN1 and IN2) be pulled up to VCC or down to GND to avoid undesired switch positions that could result from the floating pin.

Select the appropriate supply voltage to cover the entire voltage swing of the signal passing through the switch because the TS3A23159 input/output signal swing through NO and COM are dependant of the supply voltage VCC.

9.2.3 Application Curve

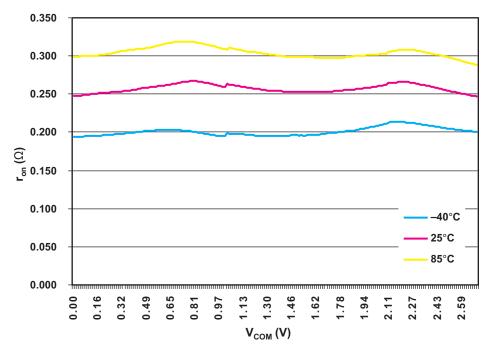


Figure 21. r_{on} vs V_{com}

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10 Power Supply Recommendations

- Proper power-supply sequencing is recommended for all CMOS devices.
- Do not exceed the absolute maximum ratings, because stresses beyond the listed ratings can cause permanent damage to the device.
- Always sequence VCC on first, followed by NO or COM.
- Although it is not required, power-supply bypassing improves noise margin and prevents switching noise propagation from the VCC supply to other components.
- A 0.1-µF capacitor, connected from VCC to GND, is adequate for most applications.

11 Layout

11.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines is recommended. Bypass capacitors must be used on power supplies. Short trace lengths should be used to avoid excessive loading.

11.2 Layout Example

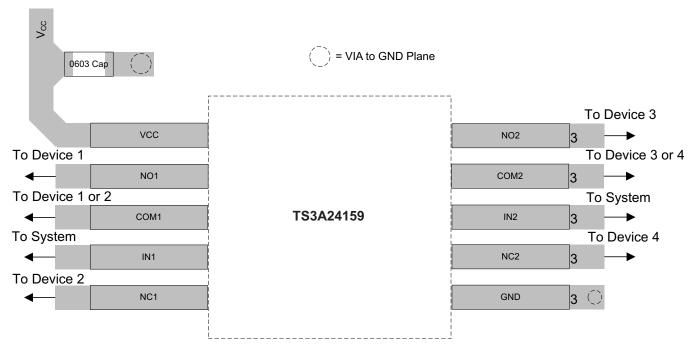


Figure 22. Layout Example



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following: Implications of Slow or Floating CMOS Inputs, SCBA004

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

E2E is a trademark of Texas Instruments.

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12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





1-Dec-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing		Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TS3A24159DGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(L8Q ~ L8R)	Samples
TS3A24159DGSRG4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(L8Q ~ L8R)	Samples
TS3A24159DRCR	ACTIVE	VSON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZWS	Samples
TS3A24159DRCRG4	ACTIVE	VSON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZWS	Samples
TS3A24159YZPR	ACTIVE	DSBGA	YZP	10	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	L87	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

1-Dec-2015

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package	Package	Pins	SPQ	Reel	Reel	Α0	В0	K0	P1	W	Pin1
201.00	Type	Drawing		0. 4	Diameter		(mm)	(mm)	(mm)	(mm)		Quadrant
TS3A24159DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS3A24159DRCR	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TS3A24159YZPR	DSBGA	YZP	10	3000	178.0	9.2	1.49	1.99	0.63	4.0	8.0	Q2

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*All dimensions are nominal

1								
	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
	TS3A24159DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0
	TS3A24159DRCR	VSON	DRC	10	3000	367.0	367.0	35.0
	TS3A24159YZPR	DSBGA	YZP	10	3000	220.0	220.0	35.0

DGS (S-PDSO-G10)

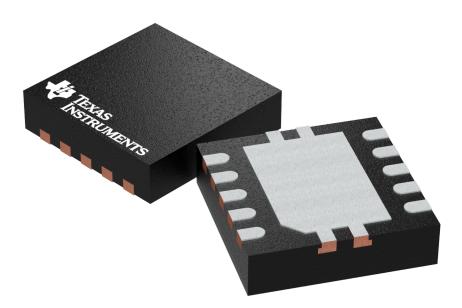
PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4204102-3/M





PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC SMALL OUTLINE - NO LEAD



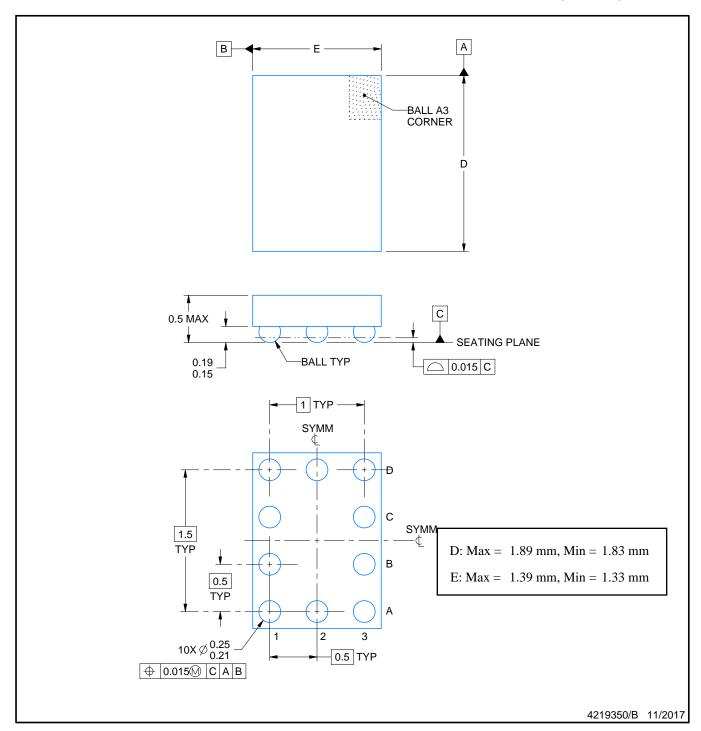
NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





DIE SIZE BALL GRID ARRAY



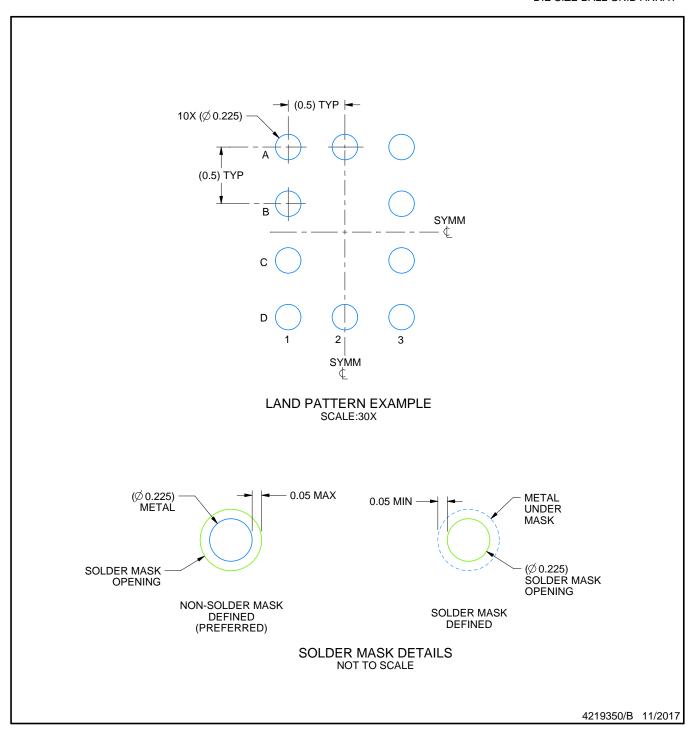
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

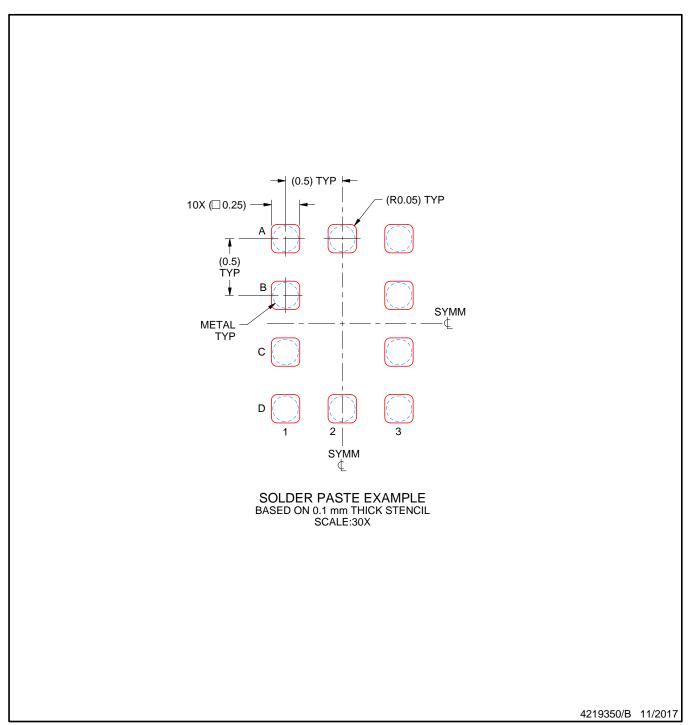


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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